

Silicon NPN Power Transistors

2SD1243

DESCRIPTION

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- With TO-3PN package
- Wide area of safe operation

APPLICATIONS

- Audio frequency power amplifier
- High frequency power amplifier

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

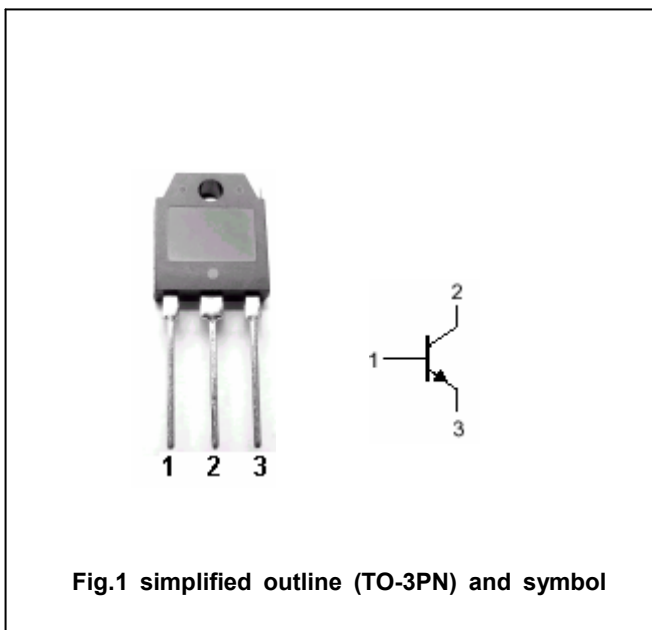


Fig.1 simplified outline (TO-3PN) and symbol

Absolute maximum ratings(Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V <sub>CBO</sub>	Collector-base voltage	Open emitter	60	V
V <sub>CEO</sub>	Collector-emitter voltage	Open base	60	V
V <sub>EBO</sub>	Emitter-base voltage	Open collector	5	V
I <sub>C</sub>	Collector current		10	A
I <sub>CM</sub>	Collector current-peak		15	A
P <sub>C</sub>	Collector power dissipation	T <sub>C</sub> =25°C	100	W
T <sub>j</sub>	Junction temperature		150	°C
T <sub>stg</sub>	Storage temperature		-55~150	°C

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## CHARACTERISTICS

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 $T_j=25^\circ\text{C}$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C=50\text{mA}; I_B=0$	60			V
$V_{(BR)CBO}$	Collector-base breakdown voltage	$I_C=1\text{mA}; I_E=0$	60			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E=1\text{mA}; I_C=0$	5			V
$V_{CEsat}$	Collector-emitter saturation voltage	$I_C=5\text{A}; I_B=0.5\text{A}$			1.5	V
$V_{BEsat}$	Base-emitter saturation voltage	$I_C=5\text{A}; I_B=0.5\text{A}$			2.0	V
$I_{CBO}$	Collector cut-off current	$V_{CB}=60\text{V}; I_E=0$			50	$\mu\text{A}$
$I_{EBO}$	Emitter cut-off current	$V_{EB}=5\text{V}; I_C=0$			50	$\mu\text{A}$
$h_{FE}$	DC current gain	$I_C=3\text{A}; V_{CE}=3\text{V}$	50			

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PACKAGE OUTLINE

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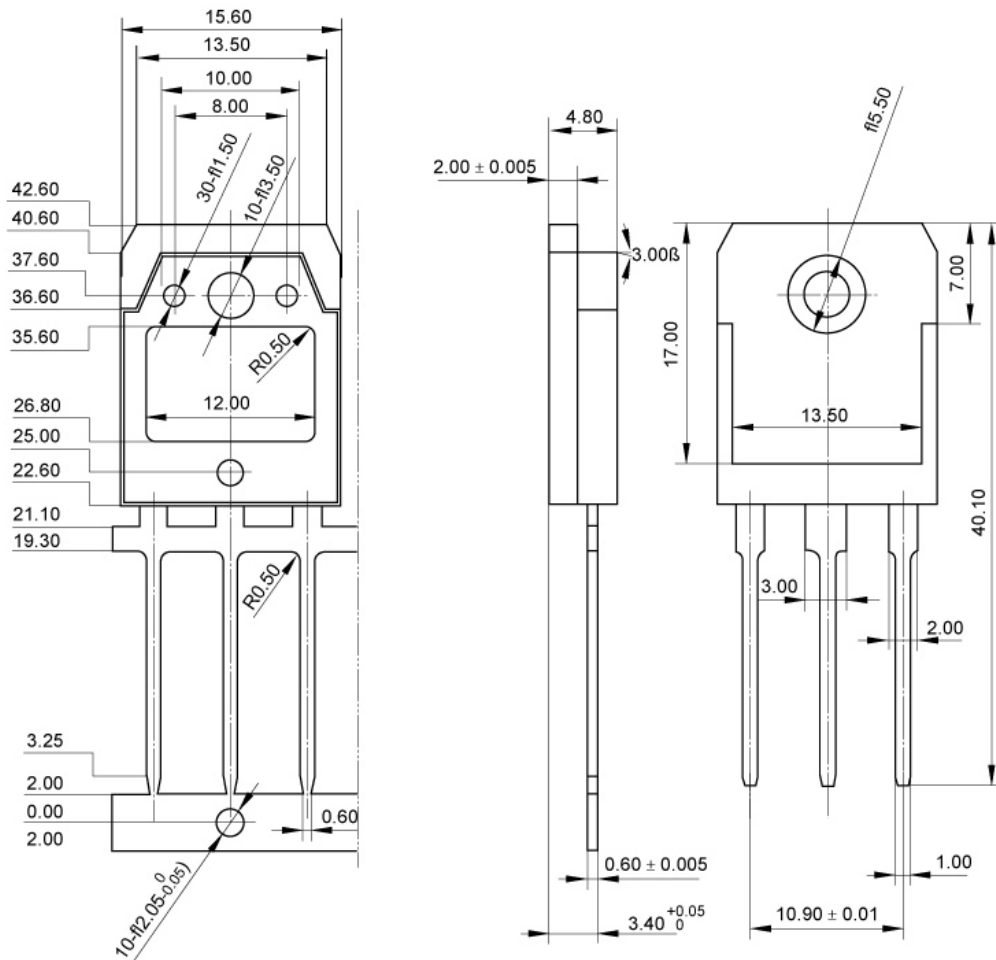


Fig.2 outline dimensions